

PLASTIC SILICON RECTIFIERS	REVERSE VOLTAGE - 50 to 1000 Volts FORWARD CURRENT - 10.0 Amperes
<p>FEATURES</p> <ul style="list-style-type: none"> ● Low cost ● Diffused junction ● Low forward voltage drop ● Low reverse leakage current ● High current capability ● The plastic material carries UL recognition 94V-0 <p>MECHANICAL DATA</p> <ul style="list-style-type: none"> ● Case: JEDEC R-6 molded plastic ● Polarity: Color band denotes cathode ● Weight: 0.07 ounces , 2.1 grams ● Mounting position: Any 	<p style="text-align: center;">R - 6</p> <p style="text-align: center;">Dimensions in inches and (millimeters)</p>

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

CHARACTERISTICS	SYMBOL	10A05	10A1	10A2	10A4	10A6	10A8	10A10	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @T _A =60°C	I _(AV)	10.0							A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load(JEDEC Method)	I _{FSM}	400							A
Maximum Forward Voltage at 10A DC	V _F	1.0							V
Maximum DC Reverse Current @T _J =25°C at Rated DC Blocking Voltage @T _J =100°C	I _R	10 100							μA
Typical Junction Capacitance (Note1)	C _J	150							pF
Typical Thermal Resistance (Note2)	R _{θJC}	6.0							°C/W
Operating Temperature Range	T _J	-55 to +125							°C
Storage Temperature Range	T _{STG}	-55 to +150							°C

NOTES:1.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

2.Thermal resistance junction to case.

FIG. 1 – FORWARD CURRENT DERATING CURVE

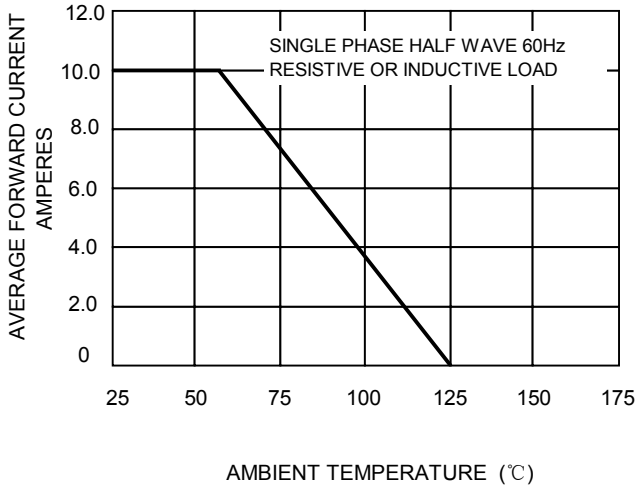


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

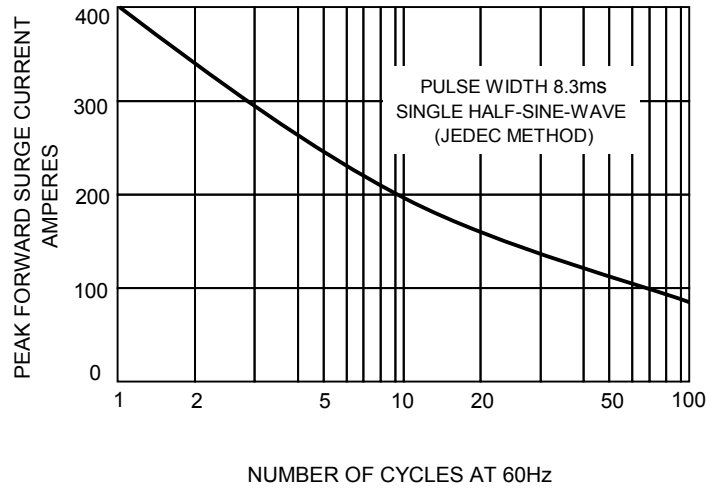


FIG.3 – TYPICAL JUNCTION CAPACITANCE

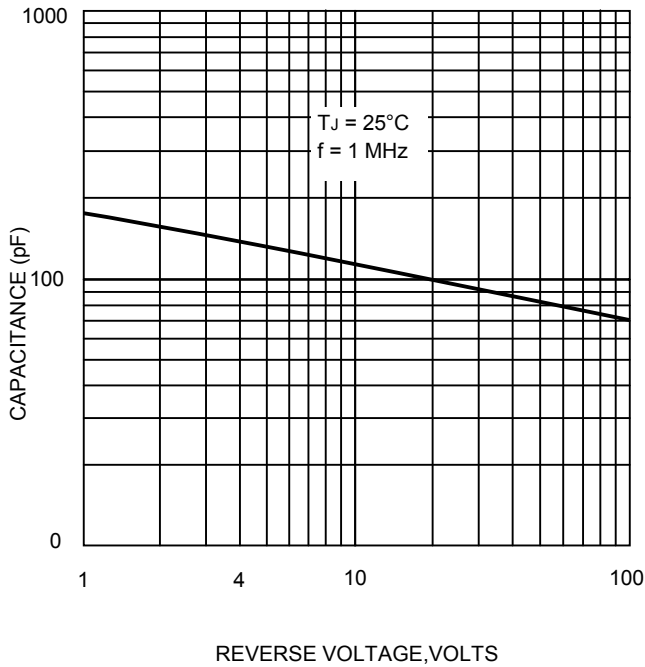


FIG.4-TYPICAL FORWARD CHARACTERISTICS

